

Silicon NPN Power Transistors

2SD1910

DESCRIPTION

- With TO-3PFM package
- High breakdown voltage
- High speed switching
- Built-in damper diode

APPLICATIONS

- For use in TV horizontal output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

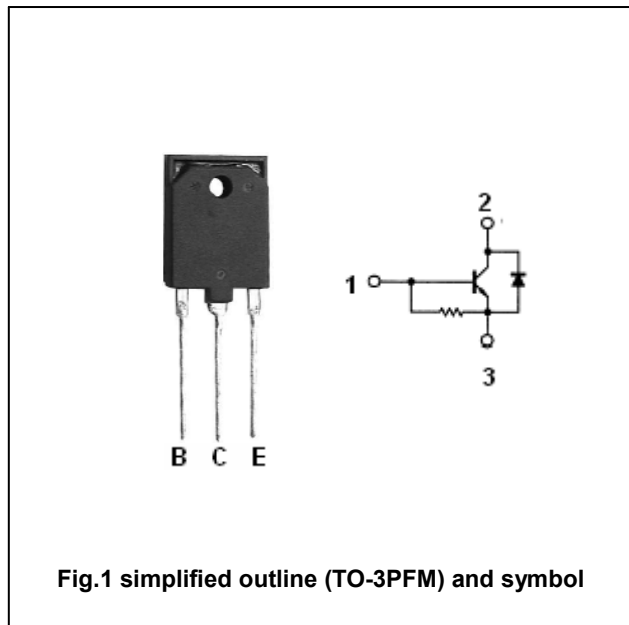


Fig.1 simplified outline (TO-3PFM) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	1500	V
V _{CEO}	Collector-emitter voltage	Open base	600	V
V _{EBO}	Emitter-base voltage	Open collector	6	V
I _C	Collector current		3	A
I _{CM}	Collector current-peak		6	A
P _C	Collector power dissipation	T _C =25□	40	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A ; I _B =0	600			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =2.5A ; I _B =0.8A			5.0	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =2.5A ; I _B =0.8A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =800V; I _E =0			10	μA
I _{EBO}	Emitter cut-off current	V _{EB} =6V; I _C =0	50		200	mA
h _{FE}	DC current gain	I _C =0.5A ; V _{CE} =5V	8		25	
V _F	Diode forward voltage	I _F =3A			2.0	V